

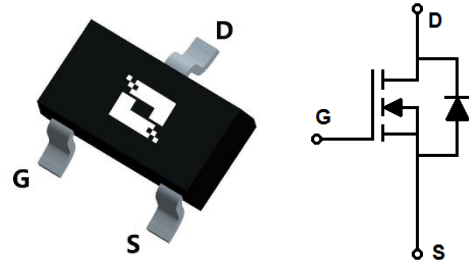
Features

- Low $R_{DS(on)}$ @ $V_{GS}=10V$
- 5V Logic Level Control
- 100% UIS Tested
- Pb-Free, RoHS Compliant

$V_{(BR)DSS}$	$R_{DS(ON)}$ Typ	I_D Max
60V	68m Ω @10V	3A
	78m Ω @4.5V	

Applications

- Load Switch
- Switching Circuits
- High Speed line Driver
- Power management


SOT23
Order Information

Product	Package	Marking	Packing
DW0633-B	SOT23	D63	3000PCS/Reel

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter		Rating	Unit
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{GS}	Gate-Source Voltage		±20	V
V _{(BR)DSS}	Drain-Source Breakdown Voltage		60	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 150	°C
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested①	T _A =25°C	23	A
I _D	Continuous Drain Current	T _A =25°C	3	A
		T _A =70°C	2.4	
P _D	Maximum Power Dissipation	T _A =25°C	1.56	W
		T _A =25°C	1.25	
R _{θC}	Thermal Resistance Junction-Ambient		80	°C/W

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	60	–	–	V
I _{DSS}	Zero Gate Voltage Drain Current(T _A =25°C)	V _{DS} =60V, V _{GS} =0V	–	–	1	μA
	Zero Gate Voltage Drain Current(T _A =125°C)	V _{DS} =48V, V _{GS} =0V	–	–	100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	–	–	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.6	--	1.8	V
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =10, I _D =3A	–	68	90	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =4.5V, I _D =2A	–	78	105	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance②	V _{GS} =3.3V, I _D =1A	--	96	130	mΩ
Dynamic Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	–	413	–	pF
C _{oss}	Output Capacitance		–	26	–	pF
C _{rss}	Reverse Transfer Capacitance		–	19	–	pF
Q _g	Total Gate Charge	V _{DS} =30V I _D =5A, V _{GS} =10V	–	10.5	–	nC
Q _{gs}	Gate Source Charge		–	1.6	–	nC
Q _{gd}	Gate Drain Charge		–	2.8	–	nC
Switching Characteristics						
t _{d(on)}	Turn on Delay Time	V _{DD} =30V, I _D =1A, R _G =3.3Ω, V _{GS} =10V	–	3.4	–	ns
t _r	Turn on Rise Time		–	5.5	–	ns
t _{d(off)}	Turn Off Delay Time		-	18	–	ns
t _f	Turn Off Fall Time		–	3.6	–	ns
Source Drain Diode Characteristics						
I _{SD}	Source drain current(Body Diode)	T _A =25°C	–	–	3	A
V _{SD}	Forward on voltage②	T _J =25°C, I _{SD} =2A, V _{GS} =0V	–	0.81	1.2	V

Notes:

① Pulse width limited by maximum allowable junction temperature ②Pulse test ; Pulse width≤300μs, duty cycle≤2%.

Typical Characteristics

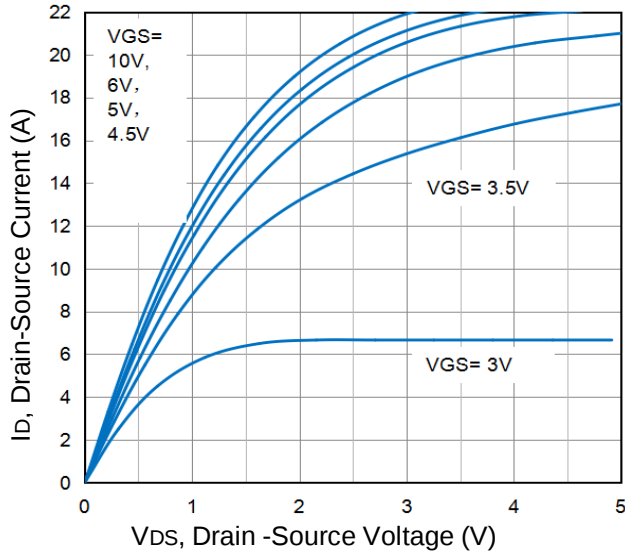


Fig1. Typical Output Characteristics

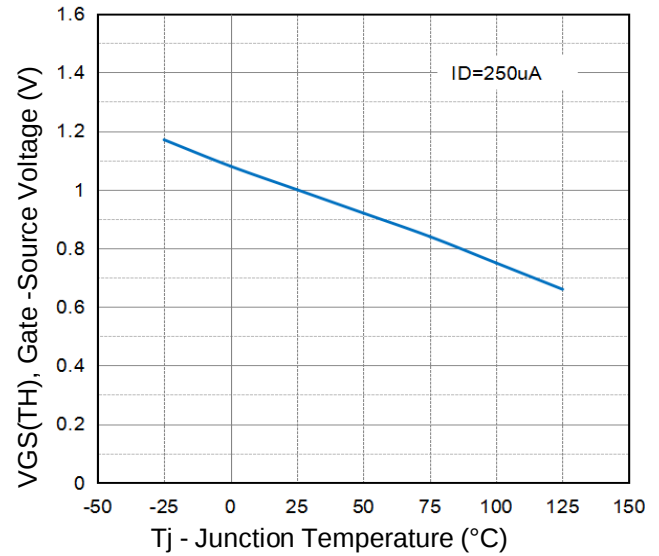


Fig2. Normalized Threshold Voltage Vs. Temperature

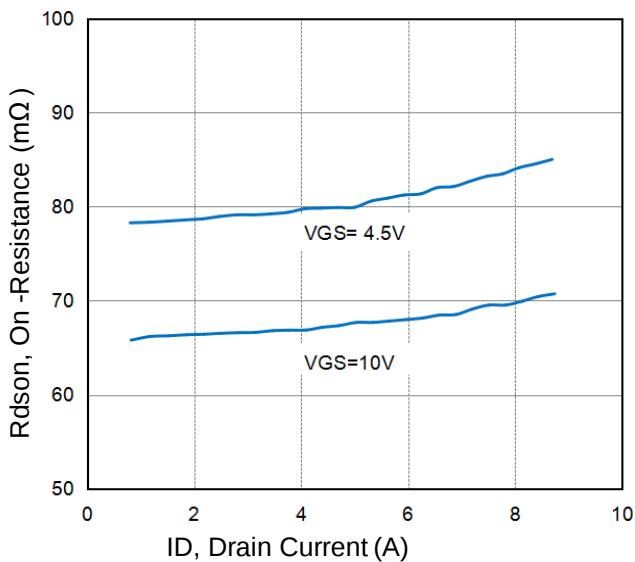


Fig3. On-Resistance vs. Drain Current and Gate

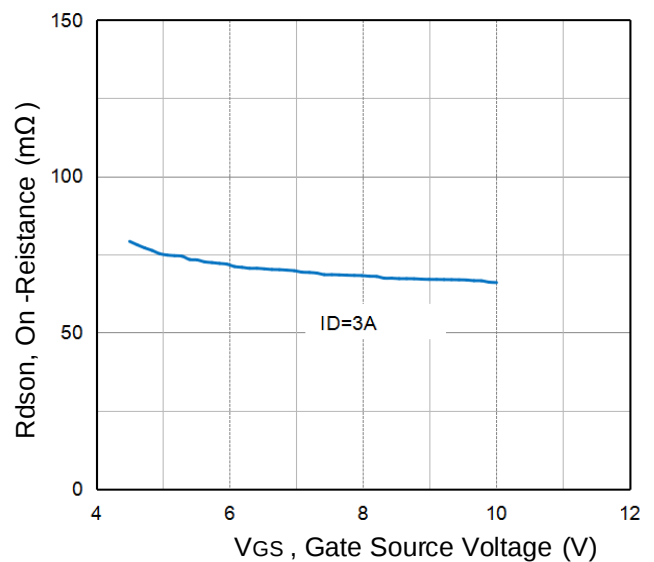


Fig4. On-Resistance vs. Gate Source Voltage

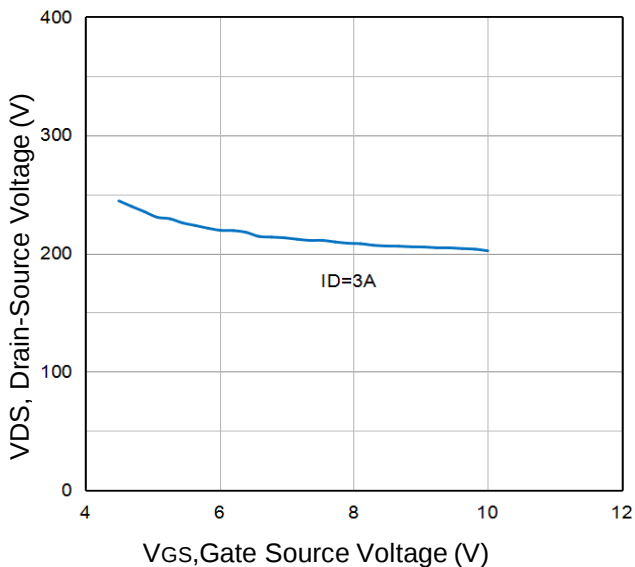


Fig5. Drain-Source Voltage vs Gate-Source Voltage

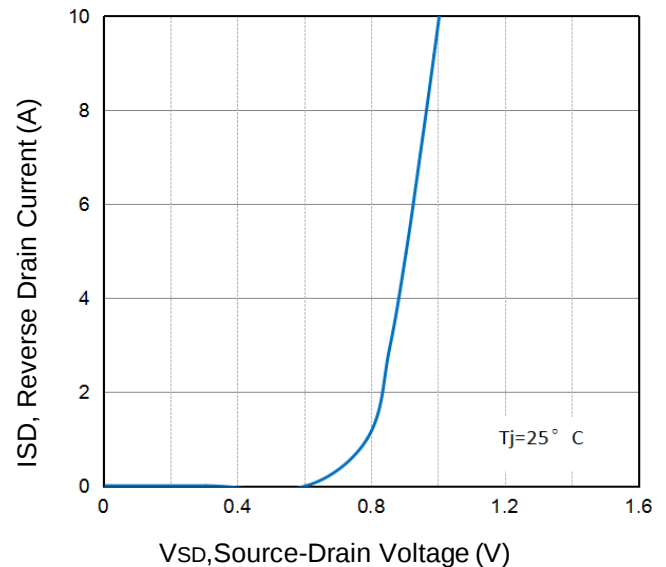


Fig6. Typical Source-Drain Diode Forward Voltage

Typical Characteristics

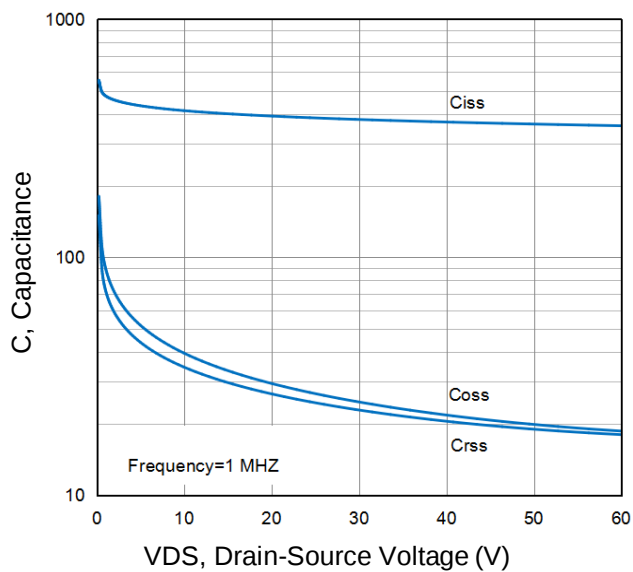


Fig7. Typical Capacitance Vs. Drain-Source Voltage

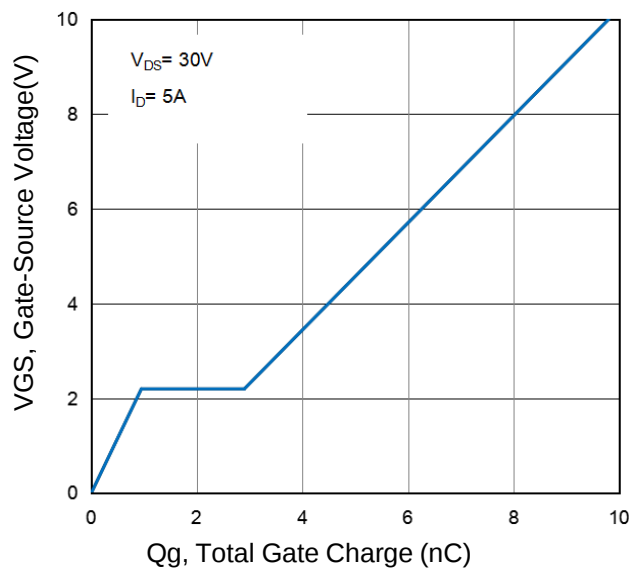
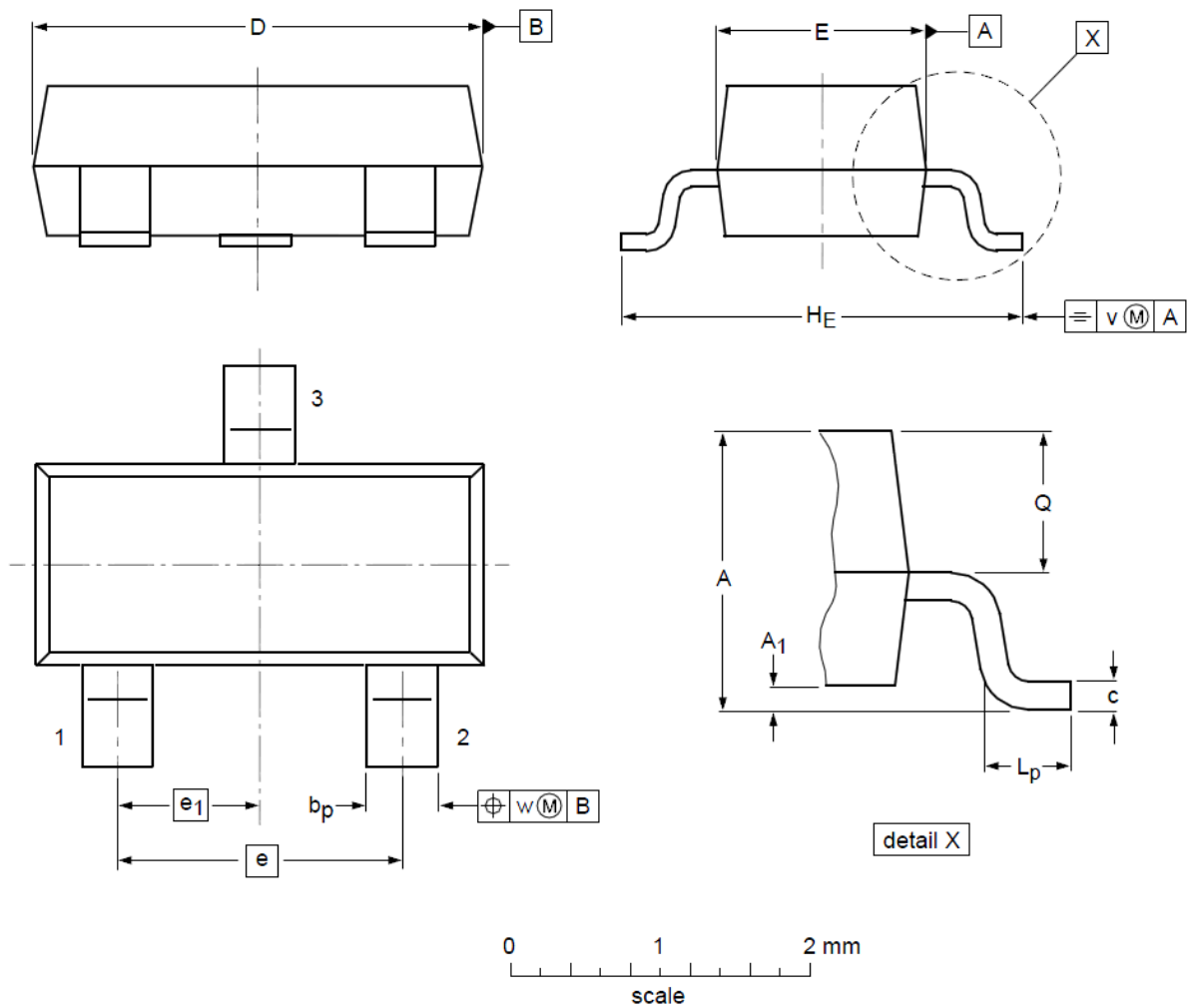


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

SOT23 Mechanical Data

DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	A₁	0.01	0.05	0.10
b_p	0.30	0.42	0.50	c	0.08	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
e	--	1.90	--	e₁	--	0.95	--
H_E	2.25	2.40	2.55	L_p	0.30	0.42	0.50
Q	0.45	0.49	0.55	v	--	0.20	--
w	--	0.10	--				

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